	Hit.		DB	Time of
	4.	(SAC or "self aligned contact") and ArF	USPAT;	Time stamp 2004/10/19 14:3
			EPO; JPO;	2004/10/19 14:1
ļ	Ĭ		DERWENT;	
2	95	(opening or trench) and (resist or	IBM_TDB	
	j	photoresist) and ("antireflective" or ADC	USPAT;	2004/10/19 14:0
		Of BARC) and (fluorocarbons or	EPO; JPO; DERWENT;	
2	100	hydrofluorocarbons)	TDM mpn	
3	130		USPAT;	2004/10/19 14:0
		Of photoresist) and ("antireflective" or	EPO; JPO;	2004/10/19 14:0
	İ	ARC OF BARC) and (fluorocarbons or	DERWENT;	
. 4	680	hydrofluorocarbons)	TDM TOO	
		(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or		2004/10/19 14:1
		"SiO.sub.2") and (SiN or "silicon	EPO; JPO;	
		nltride") and (SiON or "silicon	DERWENT;	
		oxynitride") and (CF4 or "CF sub 4" or	IBM_TDB	
		CH2F2 OF "CH. Sub. 2F. Sub. 2"\ and /overgon and		
5	422	[U.Sub.2")		
3	477	1 (opening of themen of contact) and	USPAT:	2004/10/19 14:2
	ł	(resist or photoresist) and ("silicon	EPO; JPO;	2001/10/19 14:2
		oxide" or "SiO.sub.2") and (SiN or	DERWENT;	
	ĺ	"silicon nitride") and (SiON or "silicon oxynitride") and (CF4 or "CF.sub.4" or	IBM_TDB	
		CH2F2 or "CH.sub.2F.sub.2") and (oxygen or		İ
		0.5ub.2		
6	870	(opening or trench or contact) and (modite	IJCDam.	
		or photoresist) and ("silicon ovido" or	USPAT; EPO; JPO;	2004/10/19 14:22
		1 SIU.SUD.2") and (SiN or "silicon nit mid-"	DERWENT;	
		Jor etch Stop") and (SiON or "silians	IBM TDB	
		Oxymitride" or ARC or BARC) and (CEA on		
		"CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")		
7	4977	((438/706) or (438/710) or (438/712) or		
		(438/714) or (438/720)).CCLS.	USPAT;	2004/10/19 14:13
		(100) /20/) .CCLS.	EPO; JPO;	
			DERWENT;	
9	98	((opening or trench or contact) and	IBM_TDB USPAT;	2004/10/10
	ļ	(lesist or photoresist) and ("silicon	EPO; JPO;	2004/10/19 14:14
		Oxide or "SiO.sub.2") and /SiN or	DERWENT;	
1		"silicon nitride" or "etch stop") and	IBM TDB	
1		(SiON or "silicon oxynitride" or ARC or	_	
1		BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or		
1.0	Ĭ	"O.sub.2")) and (((438/706) or (438/710)		
	1	Or (438/714) or (438/714) or		
		(438/720)).CCLS.)		
10	45	(opening or trench or contact) and (manist	USPAT;	2004/10/10 1
		or photoresist) and ("silicon ovido" on	EPO; JPO;	2004/10/19 14:14
	ł	SIU.SUD.Z") and (SiN or "siligon mitaria "	DERWENT;	
		or etch stop") and (Sion or "silian" !	IBM_TDB	
	1	oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4" or CH2F2 or "CH and OR	_	
	1	"CF.sub.4" or CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") and pattern\$4		
		and ArF		
	ı		İ	000.1
.2	5	(opening or trench or contact) and /master	TICDA	2004/10/10 14 40
.2	5	(opening or trench or contact) and (resist or photoresist) and ("silicon oxide" or	USPAT;	2004/10/19 14:18
2	5	"SiO.sub.2" or dielectric or insulation	EPO; JPO;	2004/10/19 14:18
.2	5	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "otah	EPO; JPO; DERWENT;	2004/10/19 14:18
.2	5	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oversitaide"	EPO; JPO;	2004/10/19 14:18
.2	5	"SiO. sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF cub.4")	EPO; JPO; DERWENT;	2004/10/19 14:18
.2	5	"SiO. sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F sub.2")	EPO; JPO; DERWENT;	2004/10/19 14:18
	5	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2")	EPO; JPO; DERWENT; IBM_TDB	
	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist	EPO; JPO; DERWENT; IBM_TDB	2004/10/19 14:18
	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist or photoresist or pattern\$4) and ("silicon oxide" or "SiO.sub.2" or dielectric and	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO;	
	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist or photoresist or pattern\$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or nsulating) and (SiN or "silicon pitrick"	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT;	
5	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon nitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist or photoresist or pattern\$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or insulating) and (SiON or "silicon nitride" or "etch stop") and (SiON or "silicon	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO;	
	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist or photoresist or pattern\$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT;	
	1086	"SiO.sub.2" or dielectric or insulating) and (SiN or "silicon nitride" or "etch stop") and (SiON or "silicon oxynitride" or ARC or BARC) and (CF4 or "CF.sub.4") and (CH2F2 or "CH.sub.2F.sub.2") and (oxygen or "O.sub.2") (opening or trench or contact) and (resist or photoresist or pattern\$4) and ("silicon oxide" or "SiO.sub.2" or dielectric or nsulating) and (SiN or "silicon pitrick"	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT;	

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16	104	1 (or of sell alluled confact") and	Habba	
		(Opening or trench or contact) and	USPAT;	2004/10/19 14:18
	1	(resist or photoresist or natterned) and	EPO; JPO;	1
	1	[\ Sillicon Oxide" or "SiO.sub 2" or	DERWENT;	İ
	1	dielectric or insulating) and (SiN or	IBM_TDB	1
	1	"Silicon nitride" or "etch stop") and		
	}	(SIUN OF "SILICON OXVNITTIDE" OF ADC OF	1	
		DARC) and (CF4 or "CF. sub 4" or CH2E2 or	1	
		cn.sub.2f.sub.2") and (oxygen or	1	İ
1 7		("O.sub.2"))	ĺ	ſ
17	33		Hann	1
		I ch.sub.2f.sub.2" or hydrofluorogarbon)	USPAT;	2004/10/19 14:21
		same (oxygen or "O.sub.2")	EPO; JPO;	
			DERWENT;	
18	597	I toponing of Clench or Contact) and (week-	IBM_TDB	
	1	Or photolesist) and ("silicon ovide"	USPAT;	2004/10/19 14:25
		J 510.Sub.2") and (SiN or "silicon nithis"	EPO; JPO;	
		lor etch Stop") and (Sion or "silian"	DERWENT;	
		Oxymittide" or ARC or BARC) and (CRA	IBM_TDB	ĺ
		Cr. Sub.4" Or CH2F2 Or "CH sub 2F auch 2H		1
		and toxygen or "O.sub.2") and gate	1	ļ
19	618	(opening or trench or contact) and	Hann	
		pattern\$4 and ("silicon ovide" or	USPAT;	2004/10/19 14:26
		"S10.sub.2") and (SiN or "silicon mitation	EPO; JPO;	
		or econ scop" and (sign or mail:	DERWENT;	
		ONVITLETIGE OF ARC OF BARCO STA (CD4	IBM_TDB	
	l	Or CHAPA OF CHAPA OF THE SUB-OF THE OWN		
. 1		dia (Onyqui OI (), Siin /") and wata		
20	430	(Opening or trench or contact)	HODAM	
	ļ	Parterno4 and ("silicon oridon	USPAT;	2004/10/19 14:26
		SiO. Sub.2") and (SiN or "silicon mitmid."	EPO; JPO;	
	i	or com stop and (Sion or reflices	DERWENT;	
		Oxymitride" or ARC or RARC\ and (CE4	IBM_TDB	
	ĺ	or CH2F2 or "CH sub 2F cub 2m		
		and (Oxygen of "O.Siib 2") and gatal and		
		438/\$.ccls.		